

NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

The **ASI TPV3100** is a Class AB Common Device Designed for Television Band IV & V Applications.

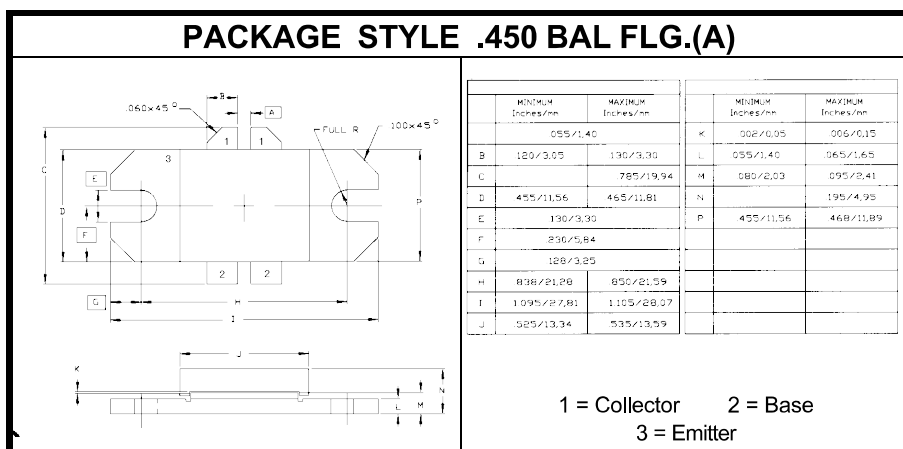
FEATURES INCLUDE:

- Gold Metalization
- Emitter Ballasting
- Internal Matching

MAXIMUM RATINGS

I_C	12 A
V_{CC}	65 V
P_{DISS}	215 W @ T _C = 25 °C
T_J	-55 °C to +200 °C
T_{STG}	-55 °C to +200 °C
q_{JC}	0.80 °C/W

PACKAGE STYLE .450 BAL FLG.(A)



CHARACTERISTICS T_C = 25 °C

SYMBOL	TEST CONDITIONS			MINIMUM	TYPICAL	MAXIMUM	UNITS
BV _{CBO}	I _C = 20 mA			65			V
BV _{CER}	I _C = 10 mA	R _{BE} = 75 Ω		30			V
BV _{EBO}	I _E = 10 mA			4.0			V
I _{CER}	V _{CE} = 28 V	R _{BE} = 75 Ω				10	mA
h _{FE}	V _{CE} = 10 V	I _C = 2.0 A		30		120	—
P _{1dB}	V _{CE} = 28 V	I _{CQ} =2X50 mA	Fo = 860 MHz	100			W
P _g	V _{CE} = 28 V	I _{CQ} =2X50 mA	Fo = 860 MHz	8.5	9.5		dB